

ENHANCED SPECIFICATION SURFACE MOUNT NPN SILICON TRANSISTOR



FEATURED ENHANCED SPECIFICATIONS:

- VCE(SAT) @ 1.0A = 0.4V MAX (from 0.5V MAX)
- hFE @ 500mA = 200 MIN (from 100 MIN)

MAXIMUM RATINGS: (T _A =25°C)	SYMBOL		UNITS
Collector-Base Voltage	V _{CBO}	80	V
Collector-Emitter Voltage	V _{CEO}	60	V
Emitter-Base Voltage	VEBO	5.0	V
Continuous Collector Current	۱ _C	1.0	А
Continuous Base Current	۱ _B	200	mA
Peak Collector Current	ICM	2.0	А
Power Dissipation	PD	350	mW
Operating and Storage Junction Temperature	T _J , T _{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

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SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
ICBO	V _{CB} =60V		100	nA
I _{EBO}	V _{EB} =4.0V		100	nA
BVCBO	Ι _C =100μΑ	80		V
BVCEO	I _C =10mA	60		V
BVEBO	I _E =100μA	5.0		V
VCE(SAT)	I _C =500mA, I _B =50mA		0.20	V
VCE(SAT)	I _C =1.0A, I _B =100mA		0.40	V
V _{BE(SAT)}	I _C =1.0A, I _B =100mA		1.1	V
VBE(ON)	V _{CE} =5.0V, I _C =1.0A		1.0	V
h _{FE} `´	V _{CE} =5.0V, I _C =1.0mA	200		
h _{FE}	V _{CE} =5.0V, I _C =500mA	200	600	
h _{FE}	V _{CE} =5.0V, I _C =1.0A	50		
h _{FE}	V _{CE} =5.0V, I _C =2.0A	15		
fT	V _{CE} =10V, I _C =50mA, f=100MHz	150		MHz
C _{ob}	V _{CB} =10V, I _E =0, f=1.0MHz		10	pF
. Enhanced and	-16 41			

Enhanced specification

R4 (27-January 2010)



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DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT491E type is an Enhanced version of the industry standard 491 NPN silicon transistor. This device is manufactured by the epitaxial planar process and epoxy molded in an SOT-23 surface mount package. The CMPT491E features Low $V_{CE(SAT)}$, high h_{FE}, and has been designed for high current general purpose amplifier applications.

MARKING CODE: C49

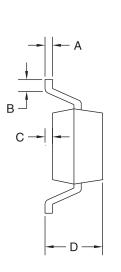
COMPLEMENTARY TYPE: CMPT591E

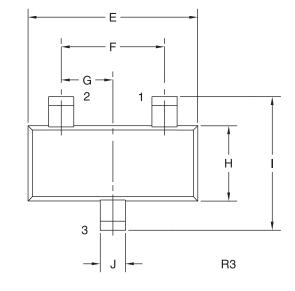




ENHANCED SPECIFICATION SURFACE MOUNT NPN SILICON TRANSISTOR

SOT-23 CASE - MECHANICAL OUTLINE





LEAD CODE:
1) Base
0) [

2) Emitter 3) Collector

MARKING CODE: C49

DIMENSIONS							
	INCHES		MILLIMETERS				
SYMBOL	MIN	MAX	MIN	MAX			
А	0.003	0.007	0.08	0.18			
В	0.006	-	0.15	-			
С	-	0.005	-	0.13			
D	0.035	0.043	0.89	1.09			
E	0.110	0.120	2.80	3.05			
F	0.075		1.90				
G	0.037		0.95				
Н	0.047	0.055	1.19	1.40			
	0.083	0.098	2.10	2.49			
J	0.014	0.020	0.35	0.50			

SOT-23 (REV: R3)

R4 (27-January 2010)

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